Preferred Device

## **Sensitive Gate Triacs**

### **Silicon Bidirectional Thyristors**

Designed for high volume, low cost, industrial and consumer applications such as motor control; process control; temperature, light and speed control.

#### **Features**

- Small Size Surface Mount DPAK Package
- Passivated Die for Reliability and Uniformity
- Four–Quadrant Triggering
- Blocking Voltage to 600 V
- On-State Current Rating of 4.0 Amperes RMS at 93°C
- Low Level Triggering and Holding Characteristics
- Epoxy Meets UL 94, V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V Machine Model, C > 400 V

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (T <sub>J</sub> = -40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open)	V <sub>DRM,</sub> V <sub>RRM</sub>	600	V
On–State RMS Current (Full Cycle Sine Wave, 60 Hz, T <sub>C</sub> = 93°C)	I <sub>T(RMS)</sub>	4.0	A
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T <sub>J</sub> = 110°C)	I <sub>TSM</sub>	40	Α
Circuit Fusing Consideration (t = 8.3 msec)	I <sup>2</sup> t	6.6	A <sup>2</sup> sec
Peak Gate Power (Pulse Width ≤ 10 μsec, T <sub>C</sub> = 93°C)	$P_{GM}$	0.5	W
Average Gate Power (t = 8.3 msec, T <sub>C</sub> = 93°C)	$P_{G(AV)}$	0.1	W
Peak Gate Current (Pulse Width $\leq$ 10 $\mu$ sec, T <sub>C</sub> = 93°C)	I <sub>GM</sub>	0.2	А
Peak Gate Voltage (Pulse Width ≤ 10 μsec, T <sub>C</sub> = 93°C)	$V_{GM}$	5.0	V
Operating Junction Temperature Range	TJ	-40 to 110	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to 150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

 V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the device are exceeded.



#### ON Semiconductor®

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# TRIACS 4.0 AMPERES RMS 600 VOLTS



#### MARKING DIAGRAMS

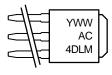


DPAK CASE 369C STYLE 6





DPAK-3 CASE 369D STYLE 6



Y = Year WW = Work Week

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance – Junction–to–Case  – Junction–to–Ambient  – Junction–to–Ambient (Note 2)	$egin{aligned} R_{ hetaJC} \ R_{ hetaJA} \ R_{ hetaJA} \end{aligned}$	3.5 88 80	°C/W
Maximum Lead Temperature for Soldering Purposes (Note 3)	T <sub>L</sub>	260	°C

#### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Peak Repetitive Blocking Current $(V_D = Rated\ V_{DRM},\ V_{RRM};\ Gate\ Open) \\ T_J = 25^{\circ}C \\ T_J = 110^{\circ}C$	I <sub>DRM,</sub> I <sub>RRM</sub>	- -	_ _	0.01 2.0	mA
ON CHARACTERISTICS					
Peak On–State Voltage (Note 4) (I <sub>TM</sub> = ±6.0 A)	V <sub>TM</sub>	-	1.3	1.6	V
Gate Trigger Current (Continuous dc) ( $V_D$ = 12 V, $R_L$ = 100 $\Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	l <sub>GT</sub>	- - - -	1.8 2.1 2.4 4.2	3.0 3.0 3.0 5.0	mA
Gate Trigger Voltage (Continuous dc) ( $V_D$ = 12 V, $R_L$ = 100 $\Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	V <sub>GT</sub>	0.5 0.5 0.5 0.5	0.62 0.57 0.65 0.74	1.3 1.3 1.3 1.3	V
Gate Non–Trigger Voltage $(V_D = 12 \text{ V}, \text{ R}_L = 100 \ \Omega, \text{ T}_J = 110^{\circ}\text{C})$ MT2(+), G(+); MT2(+), G(-); MT2(-), G(-); MT2(-), G(+)	V <sub>GD</sub>	0.1	0.4	_	V
Holding Current (V <sub>D</sub> = 12 V, Gate Open, Initiating Current = ±200 mA)	lн	-	1.5	15	mA
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	IL	- - - -	1.75 5.2 2.1 2.2	10 10 10 10	mA

#### **DYNAMIC CHARACTERISTICS**

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current ( $V_D$ = 200 V, $I_{TM}$ = 1.8 A, Commutating dv/dt = 1.0 V/ $\mu$ sec, $T_J$ = 110°C, f = 250 Hz, CL = 5.0 $\mu$ fd, LL = 80 mH, RS = 56 $\Omega$ , CS = 0.03 $\mu$ fd) With snubber see Figure 11	di/dt(c)	-	3.0	-	A/ms
Critical Rate of Rise of Off–State Voltage $(V_D = 0.67 \text{ X Rated } V_{DRM}, \text{ Exponential Waveform,}$ Gate Open, $T_J = 110^{\circ}\text{C})$	dv/dt	10	-	-	V/μs

- 2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.
- 3. 1/8" from case for 10 seconds.
- 4. Pulse Test: Pulse Width ≤ 2.0 msec, Duty Cycle ≤ 2%.

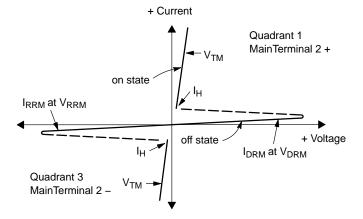
#### **ORDERING INFORMATION**

Device	Package Type	Package	Shipping <sup>†</sup>
MAC4DLM-001	DPAK-3	369D	75 Units / Rail
MAC4DLMT4	DPAK	369C	16 mm Tape & Reel (2.5 k / Reel)

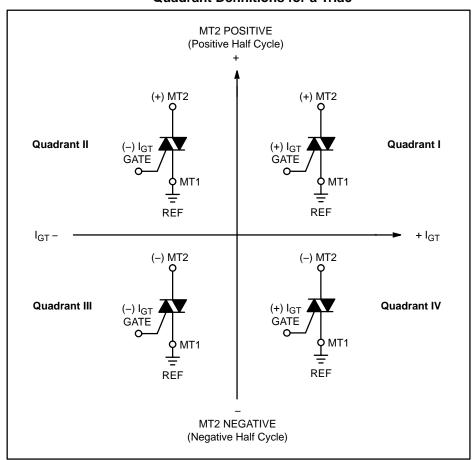
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off-State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off–State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On–State Voltage
I <sub>H</sub>	Holding Current



#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

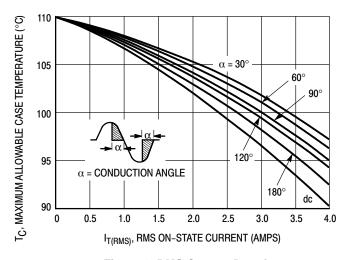


Figure 1. RMS Current Derating

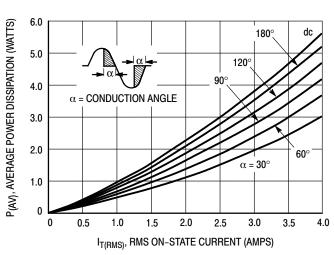


Figure 2. On-State Power Dissipation

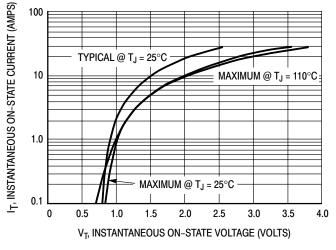
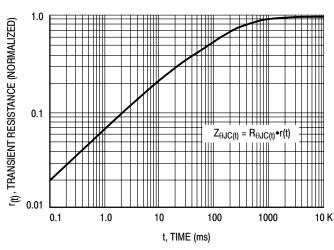


Figure 3. On-State Characteristics



**Figure 4. Transient Thermal Response** 

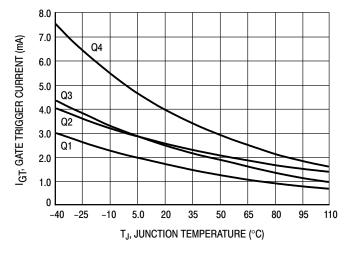


Figure 5. Typical Gate Trigger Current versus
Junction Temperature

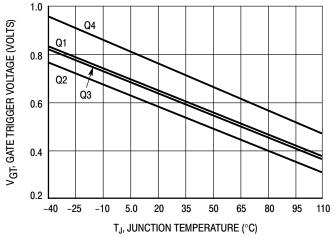
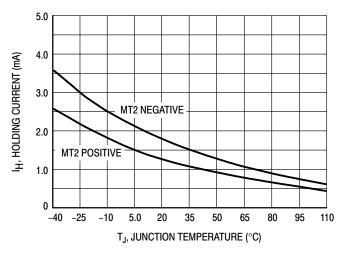


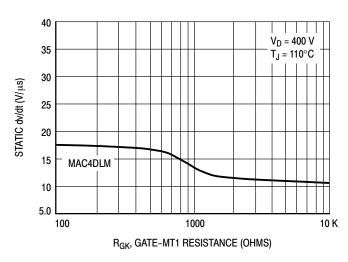
Figure 6. Typical Gate Trigger Voltage versus
Junction Temperature



12 10 IL, LATCHING CURRENT (mA) 8.0 Q2 6.0 4.0 2.0 0 -25 -40 -10 5.0 20 35 50 65 80 95 110 T<sub>.I</sub>, JUNCTION TEMPERATURE (°C)

Figure 7. Typical Holding Current versus Junction Temperature

Figure 8. Typical Latching Current versus Junction Temperature



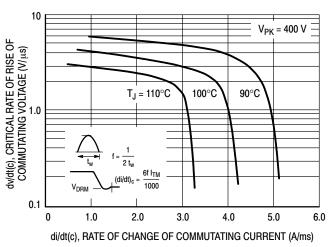
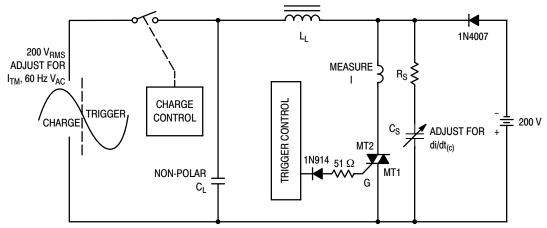


Figure 9. Minimum Exponential Static dv/dt versus Gate-MT1 Resistance

Figure 10. Critical Rate of Rise of Commutating Voltage

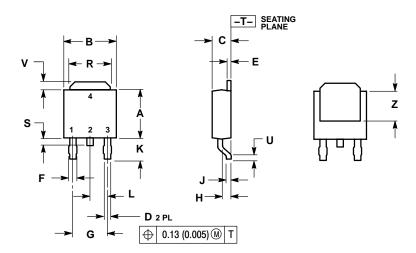


Note: Component values are for verification of rated (di/dt)<sub>c</sub>. See AN1048 for additional information.

Figure 11. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)<sub>c</sub>

#### **PACKAGE DIMENSIONS**

#### **DPAK** CASE 369C **ISSUE O**

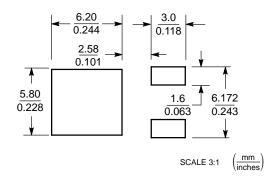


- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		INCHES MILLIN		MILLIM	METERS	
DIM	MIN	MAX	MIN	MAX			
Α	0.235	0.245	5.97	6.22			
В	0.250	0.265	6.35	6.73			
С	0.086	0.094	2.19	2.38			
D	0.027	0.035	0.69	0.88			
Е	0.018	0.023	0.46	0.58			
F	0.037	0.045	0.94	1.14			
G	0.180	BSC	4.58 BSC				
Н	0.034	0.040	0.87	1.01			
J	0.018	0.023	0.46	0.58			
K	0.102	0.114	2.60	2.89			
L	0.090 BSC		2.29 BSC				
R	0.180	0.215	4.57	5.45			
S	0.025	0.040	0.63	1.01			
U	0.020		0.51				
٧	0.035	0.050	0.89	1.27			
7	0.155		3 93				

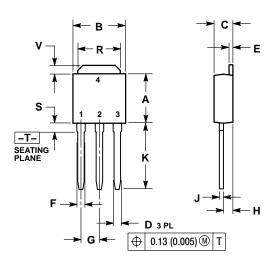
# STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2

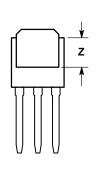
#### **SOLDERING FOOTPRINT**



#### **PACKAGE DIMENSIONS**

DPAK-3 CASE 369D-01 **ISSUE B** 





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	0.090 BSC		BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
٧	0.035	0.050	0.89	1.27
Z	0.155		3.93	

- STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2

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